L Number	Hits	Search Text	DB	Time stamp
1	49892	isotrop$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:43
2	3802	l adj shap$2 same spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:45
3	4822	((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:43
4	13856	isotrop$5 near5 etch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:44
5	52320	(isotrop$5 or wet) near5 etch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:48
6	54	((isotrop$5 or wet) near5 etch$3) same (l adj shap$2 same spacer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:44
7	346624	spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:45
8	3851	((isotrop$5 or wet) near5 etch$3) same spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:45
9	189323	l adj shap$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:46
10	54	(((isotrop$5 or wet) near5 etch$3) same spacer$1) same (l adj shap$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:48
11	23	(((((isotrop$5 or wet) near5 etch$3) same spacer$1) same (l adj shap$2)) and ((isotrop$5 or wet) near5 etch$3 near10 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:49
16	2	"6518136"	USPAT	2004/06/17 19:07
19	3	("5716862" | "6025267" | "6165826").PN.	USPAT	2004/06/17 19:12
20	13	("4038107" | "4638347" | "4697199" | "4735680" | "4764477" | "4818714" | "4843023" | "4851730" | "4853352" | "4981810" | "5183770" | "5221632" | "5256586").PN.	USPAT	2004/06/17 19:35
21	41	5573965.URPN.	USPAT	2004/06/17 19:35
-	0	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj sustrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:46

-	319	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:34
-	0	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:06
-	147	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (protective adj layer$1 or (film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:27
-	0	((((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)) and (sidewall or (side adj wall) with protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:24
-	0	((((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)) and (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:09
-	12	((((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (protective adj layer$1 or (film$1))) and (first adj impurit$3) and (second adj impurit$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:11
-	392	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:18
-	361	(((gate adj dielectric) same ((gate adj electrode)) with (semiconductor adj substrate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:19
-	333	(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:35
-	333	((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:24
-	138	(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)) and (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:36
-	72	((((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)) and (sidewall or (side adj wall))) and (protective adj layer$1 or (film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:37
-	103052	(metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 13:35

-	53	((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same ((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:35
-	62	((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:35
-	0	((((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) same (protective adj layer$1 or (film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:38
-	20	(((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) and (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:37
-	0	((((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) and (protective adj layer$1 or (film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:40
-	2	(((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:49
-	2	((((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) and ((protective or (insulat$3)) adj layer$1 or (film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:48
-	6770	gate adj dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:47
-	2280	(gate adj dielectric) same (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:48
-	803	((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:49
-	138	(((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))) same (sidewall or (side adj wall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:50
-	7	(((((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))) same (sidewall or (side adj wall))) same (sidewall or (side adj wall) adj mask$1)) same (ion adj implant$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:53

-	105	((((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))) same (sidewall or (side adj wall))) same (sidewall or (side adj wall) adj mask$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:54
-	2009	((438/301) or (438/303) or (438/305)).CCLS.	USPAT; US-PGPUB	2004/06/17 15:22
-	2774	((438/301) or (438/303) or (438/305)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 11:53
-	0	(((438/301) or (438/303) or (438/305)).CCLS.) and (dual adj spacer) same (implant$3 with extension)	USPAT; US-PGPUB	2002/05/15 11:54
-	0	(((438/301) or (438/303) or (438/305)).CCLS.) and (dual adj spacer) same (implant$3 with extension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 11:56
-	1	("6287920").PN.	USPAT; US-PGPUB	2002/05/15 11:56
-	130	(((438/301) or (438/303) or (438/305)).CCLS.) and (implant$3 with extension)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:51
-	117	(mos adj transisor) or (metal adj oxide adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 17:05
-	297	((mos adj transisor) or (metal adj oxide adj transistor)) with (plural adj dop$3) or ((first adj dop$3) with (second adj dop$3) with (third adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 17:08
-	4	(((mos adj transisor) or (metal adj oxide adj transistor)) with (plural adj dop$3) or ((first adj dop$3) with (second adj dop$3) with (third adj dop$3))) with (ion adj implant$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 17:10
-	6	(((mos adj transisor) or (metal adj oxide adj transistor)) with (plural adj dop$3) or ((first adj dop$3) with (second adj dop$3) with (third adj dop$3))) with extension	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 17:10
-	11	l adj shap$2 with sidewall$1 and extension$1 and implant$3 and dop$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:23
-	5	l adj shap$2 with sidewall$1 and extension$1 and implant$3 and dop$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:16
-	16	l adj shap$2 with sidewall$1 and implant$3 and dop$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 18:16
-	0	l adj shap$2 with sidewall$1 and implant$3 and dop$3 and boron and boron adj florine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:24
-	16	l adj shap$2 with sidewall$1 and implant$3 and dop$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:27

-	156	l adj shap$2 and implant$3 and dop$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:28
-	68	l adj shap$2 and mos and implant$3 and dop$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:49
-	166723	l adj shap$2 mdd with implant$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:50
-	1	l adj shap$2 and mdd with implant$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:51
-	0	l adj shap$2 with side adj wall$ and mdd with implant$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:52
-	21	mos and mdd with implant$3 and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 11:52
-	15	pmos and mdd and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/10 12:42
-	56729	anisotrop$$5	USPAT; US-PGPUB	2003/02/21 17:28
-	3	isostrop$5	USPAT; US-PGPUB	2003/02/21 17:28
-	28701	isotrop$5	USPAT; US-PGPUB	2004/06/17 18:42
-	15001	anisotrop$$5 and isotrop$5	USPAT; US-PGPUB	2003/02/21 17:29
-	342575	gate	USPAT; US-PGPUB	2003/02/21 17:29
-	4331	(anisotrop$$5 and isotrop$5) and gate	USPAT; US-PGPUB	2003/02/21 17:30
-	39483	ion adj implant$5	USPAT; US-PGPUB	2003/02/21 17:30
-	1875	((anisotrop$$5 and isotrop$5) and gate) and (ion adj implant$5)	USPAT; US-PGPUB	2003/02/21 17:30
-	432112	extension	USPAT; US-PGPUB	2003/02/21 17:31
-	367	(((anisotrop$$5 and isotrop$5) and gate) and (ion adj implant$5)) and extension	USPAT; US-PGPUB	2003/02/21 17:31
-	9	("4908326" | "5234850" | "5501997" | "5541132" | "5679589" | "5770508" | "5783475" | "5863824" | "6020242").PN.	USPAT	2003/02/21 17:57
-	2768	l adj shap$2 same spacer$1	USPAT; US-PGPUB	2004/06/17 18:43
-	5	(((((anisotrop$$5 and isotrop$5) and gate) and (ion adj implant$5)) and extension) and (l adj shap$2 same spacer$1)	USPAT; US-PGPUB	2003/02/21 18:01
-	42115	anisotropic or anisotropical	USPAT; US-PGPUB	2003/05/14 09:51
-	29071	isotropic or isotropical	USPAT; US-PGPUB	2003/05/14 09:52
-	7380	(anisotropic or anisotropical) same (isotropic or isotropical)	USPAT; US-PGPUB	2003/05/14 09:53
-	2340873	side adj wall or side	USPAT; US-PGPUB	2003/05/14 09:53

-	185606	mask	USPAT; US-PGPUB	2003/05/14 09:53
-	7009	(side adj wall or side) near2 mask	USPAT; US-PGPUB	2003/05/14 09:54
-	234	((anisotropic or anisotropical) same (isotropic or isotropical)) and ((side adj wall or side) near2 mask)	USPAT; US-PGPUB	2003/05/14 09:54
-	3	("5770508" | "5783475" | "5817563").PN.	USPAT	2003/05/14 09:57
-	6	("4784965" | "4855247" | "5024959" | "5153145" | "5234850" | "5472896").PN.	USPAT	2003/05/14 09:58
-	19	5770508.URPN.	USPAT	2003/05/14 09:59
-	2	6197648.URPN.	USPAT	2003/05/14 10:01
-	3802	1 adj shap$2 same spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 13:21
-	424360	(metal adj oxide adj field adj effect adj transistor$1)or MOS or MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 13:36
-	195	(1 adj shap$2 same spacer$1) and ((metal adj oxide adj field adj effect adj transistor$1)or MOS or MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 13:37
-	4822	((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:43
-	65	(((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.) and (1 adj shap$2 same spacer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 15:28